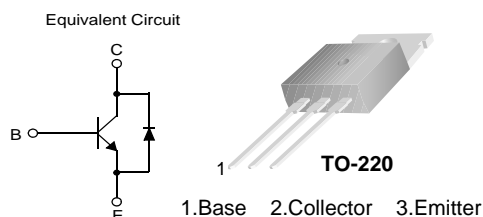


KSC5603D

NPN Silicon Transistor, Planar Silicon Transistor

Features

- High Voltage High Speed Power Switch Application
- Wide Safe Operating Area
- Built-in Free Wheeling Diode
- Suitable for Electronic Ballast Application
- Small Variance in Storage Time



Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	1600	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	12	V
I_C	Collector Current (DC)	3	A
I_{CP}	*Collector Current (Pulse)	6	A
I_B	Base Current (DC)	2	A
I_{BP}	*Base Current (Pulse)	4	A
P_C	Power Dissipation($T_C=25^\circ\text{C}$)	100	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	-65 to +150	$^\circ\text{C}$

* Pulse Test: Pulse Width=5ms, Duty Cycle \leq 10%

Thermal Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter		Rating	Units
$R_{\theta JC}$	Thermal Resistance	Junction to Case	1.25	$^\circ\text{C/W}$
$R_{\theta JA}$		Junction to Ambient	80	$^\circ\text{C/W}$
T_L	Maximun Lead Temperature for Soldering Purpose : 1/8" from Case for 5 seconds		270	$^\circ\text{C}$

Electrical Characteristics $T_A=25^\circ\text{C}$ unless otherwise noted

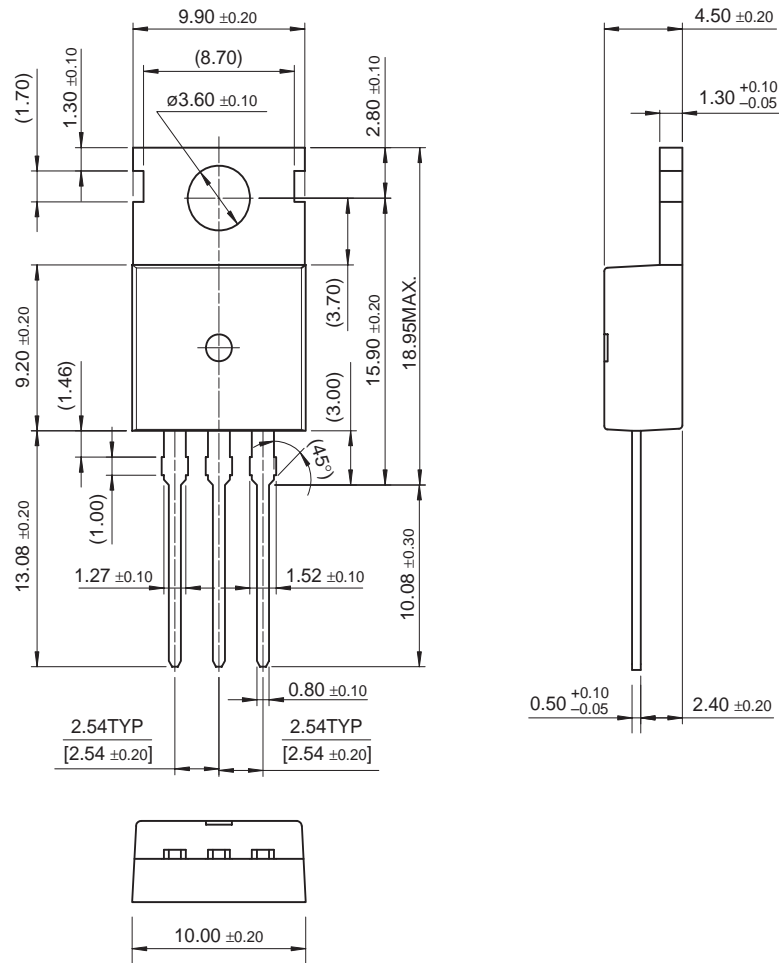
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C=0.5\text{mA}, I_E=0$	1600	1689		V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C=5\text{mA}, I_B=0$	800	870		V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E=0.5\text{mA}, I_C=0$	12	14.8		V
I_{CES}	Collector Cut-off Current	$V_{CES}=1600\text{V}, I_E=0$	$T_A=25^\circ\text{C}$	0.01	100	μA
			$T_A=125^\circ\text{C}$		1000	μA
I_{CEO}	Collector Cut-off Current	$V_{CE}=800\text{V}, V_{BE}=0$	$T_A=25^\circ\text{C}$	0.01	100	μA
			$T_A=125^\circ\text{C}$		1000	μA
I_{EBO}	Emitter Cut-off Current	$V_{EB}=12\text{V}, I_C=0$		0.05	500	μA
h_{FE}	DC Current Gain	$V_{CE}=3\text{V}, I_C=0.4\text{A}$	$T_A=25^\circ\text{C}$	20	29	35
			$T_A=125^\circ\text{C}$	6	15	
		$V_{CE}=10\text{V}, I_C=5\text{mA}$	$T_A=25^\circ\text{C}$	20	43	
			$T_A=125^\circ\text{C}$	20	46	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=250\text{mA}, I_B=25\text{mA}$	$T_A=25^\circ\text{C}$	0.5	1.25	V
			$T_A=125^\circ\text{C}$			V
		$I_C=500\text{mA}, I_B=50\text{mA}$	$T_A=25^\circ\text{C}$	1.5	2.5	V
			$T_A=125^\circ\text{C}$			V
		$I_C=1\text{A}, I_B=0.2\text{mA}$	$T_A=25^\circ\text{C}$	1.2	2.5	V
			$T_A=125^\circ\text{C}$			V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=500\text{mA}, I_B=50\text{mA}$	$T_A=25^\circ\text{C}$	0.74	1.2	V
			$T_A=125^\circ\text{C}$	0.61	1.1	V
		$I_C=2\text{A}, I_B=0.4\text{A}$	$T_A=25^\circ\text{C}$	0.85	1.2	V
			$T_A=125^\circ\text{C}$	0.74	1.1	V
C_{ib}	Input Capacitance	$V_{EB}=10\text{V}, I_C=0, f=1\text{MHz}$		745	1000	pF
C_{ob}	Output Capacitance	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$		56	500	pF
f_T	Current Gain Bandwidth Product	$I_C=0.1\text{A}, V_{CE}=10\text{V}$		5		MHz
V_F	Diode Forward Voltage	$I_F=0.4\text{A}$	$T_A=25^\circ\text{C}$	0.76	1.2	V
			$T_A=125^\circ\text{C}$			V
		$I_F=1\text{A}$	$T_A=25^\circ\text{C}$	0.83	1.5	V
			$T_A=125^\circ\text{C}$			V

Electrical Characteristics (Continued) $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition		Min.	Typ.	Max.	Units
RESISTIVE LOAD SWITCHING (D.C ≤ 10%, Pulse Width=20μs)							
t _{ON}	Turn On Time	I _C =0.3A, I _{B1} =50mA, I _{B2} =150A, V _{CC} =125V, R _L = 416Ω	T _A =25°C		400	600	ns
			T _A =125°C				ns
t _{STG}	Storage Time		T _A =25°C	2.0	2.1	2.3	μs
			T _A =125°C				μs
t _F	Fall Time		T _A =25°C		310	1000	ns
			T _A =125°C				ns
t _{ON}	Turn On Time	I _C =0.5A, I _{B1} =50mA, I _{B2} =250mA, V _{CC} =125V, R _L = 250Ω	T _A =25°C		600	1100	ns
			T _A =125°C				ns
t _{STG}	Storage Time		T _A =25°C		1.3	1.5	μs
			T _A =125°C				μs
t _F	Fall Time		T _A =25°C		180	350	ns
			T _A =125°C				ns
INDUCTIVE LOAD SWITCHING (V _{CC} =15V)							
t _{ON}	Turn On Time	I _C =0.3A, I _{B1} =50mA, I _{B2} =150mA, V _Z =300V, L _C =200H	T _A =25°C	0.6	0.73	0.9	μs
			T _A =125°C				μs
t _{STG}	Storage Time		T _A =25°C		170	250	ns
			T _A =125°C				ns
t _F	Fall Time	I _C =0.3A, I _{B1} =50mA, I _{B2} =150mA, V _Z =300V, L _C =200H	T _A =25°C		180	250	ns
			T _A =125°C				ns
t _{ON}	Turn On Time	I _C =0.5A, I _{B1} =50mA, I _{B2} =250mA, V _Z =300V, L _C =200H	T _A =25°C	0.7	0.84	1.0	μs
			T _A =125°C				μs
t _{STG}	Storage Time		T _A =25°C		140	175	ns
			T _A =125°C				ns
t _F	Fall Time	I _C =0.5A, I _{B1} =50mA, I _{B2} =250mA, V _Z =300V, L _C =200H	T _A =25°C		170	200	ns
			T _A =125°C				ns

Physical Dimension

TO-220





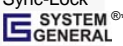


Dimensions in Millimeters



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